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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/766,116	01/27/2004	Daniel C. Guterman	SAND-01016US0	3156
28554	7590 09/08/2005		EXAMINER	
	AGEN MARCUS HAR	NGUYEN, VIET Q		
685 MARKET STREET, SUITE 540 SAN FRANCISCO, CA 94105			ART UNIT	PAPER NUMBER
	,		2827	

DATE MAILED: 09/08/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(a)			
Office Action Summary		10/766,116	Applicant(s) GUTERMAN ET AL.			
		Examiner	Art Unit			
		Viet Q. Nguyen	2827			
	The MAILING DATE of this communication app					
Period fo	or Reply					
WHIC - Exter after - If NO - Failu Any r	ORTENED STATUTORY PERIOD FOR REPLY CHEVER IS LONGER, FROM THE MAILING DANSIONS of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. It period for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION 36(a). In no event, however, may a reply be tin will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	N. nely filed the mailing date of this communication. (D) (35 U.S.C. § 133).			
Status						
1)⊠	Responsive to communication(s) filed on Elect	<u>ion filed on 8/11/2005</u> .				
,		2b)⊠ This action is non-final.				
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is					
	closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.			
Dispositi	on of Claims					
5)⊠ 6)⊠ 7)⊠	Claim(s) <u>27-45</u> is/are pending in the application 4a) Of the above claim(s) is/are withdraw Claim(s) <u>38-45</u> is/are allowed. Claim(s) <u>27,28,33,35 and 36</u> is/are rejected. Claim(s) <u>29-32,34 and 37</u> is/are objected to. Claim(s) are subject to restriction and/o	vn from consideration.	£			
Applicati	ion Papers	·				
10)	The specification is objected to by the Examine The drawing(s) filed on is/are: a) accomplicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the Example 2.	epted or b) objected to by the drawing(s) be held in abeyance. Se tion is required if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR 1.121(d).			
Priority (ınder 35 U.S.C. § 119					
12) a)	Acknowledgment is made of a claim for foreign All b) Some * c) None of: 1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority document application from the International Bureau See the attached detailed Office action for a list	s have been received. s have been received in Applicat rity documents have been receive u (PCT Rule 17.2(a)).	ion No ed in this National Stage			
2) Notice	nt(s) the of References Cited (PTO-892) the of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/08) the No(s)/Mail Date 2/17, 6/17, 6/27, 08 0≤	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal I 6) Other:				

DETAILED ACTION

1. Claims **27-45** are present for examination.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claim 27-28, 33, 35-36 are rejected under 35 U.S.C. 103(a) as being unpatentable over Holzmann et al (US 6,301,161).

Regarding claim 27, Holzman et al (see Fig. 1) shows a circuit for programming a non-volatile memory cell (flash cell 120) which has a capability of providing "coarse amplitudes (voltage)" for coarse programming phase and also "fine amplitudes (voltage)" for fine programming phase. Fig. 3 shows a similar claimed programming method that utilize both coarse and fine programming phases, and such that a fine programming phase (begins at step 340) follows after the coarse programming phase (begins at step 310). It is noted that although this reference does not specifically mention the word "metering charge"; however, Fig. 2 of this reference already shows the appropriate circuitry for providing appropriate programming voltage pulses and/or current pulses to the control gate of the memory cell (210), and their amplitudes can be adjusted or varied base don programming time and/or verification process. Thus, as

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time progrsess4es, the charge that could be stored and/or accumulated onto the floating (per each fine programming step) can be finely controlled, measured, injected, or "metered" carefully as well. For example, col. 4 (lines 55-61) stated that "... the absolute value change of the floating gate voltage depends on the programming time, the programming current Ip (242) and the applied voltage Vpdp (222) and Vsgp (232)". Thus, in so far as programming verification is concerned, the stored charges on the floating gate can be stored, read out, compared, decided, and metered gradually as "increasing" or "decreasing", if any, as desired without any complicated circuitry required to one skilled in this art. As a result, charges can be "metered" in or out obviously using just these voltage and/or current switches based on programming time without further complicated circuitry for example.

Regarding claim 28, Fig. 3 shows that fine programming is carried out right after coarse programming phase;

Regarding claim **33 & 35**, Fig. 2 shows that a plurality of voltage switches for switching power supplies to the floating gate of such non-volatile cell. Furthermore, the coarse programming phase/mode does not use any metering charge techniques.

4. Claim **27-28**, **33**, **35-36** are rejected under 35 U.S.C. 103(a) as being unpatentable over **Mokhlesi et al (6,856,551)**.

Regarding claim 27, Mokhlesi et al (see Fig. 5) shows a similar claimed programming method that utilize both coarse and fine programming phases, and such that a fine programming phase (begins at step 529) follows after the coarse

programming phase (begins at step 503). It is noted that although this reference does not specifically mention the word "metering charge"; however, Fig. 4A-4B of this reference already shows the appropriate circuitry for providing appropriate programming voltage pulses and/or programming current pulses to the control gate of the memory cell (411, 413, 415) using switches (421), and their amplitudes can be adjusted or varied based on programming time and/or programming verification process. Thus, as time progrsess4es, the charges that could be stored and/or accumulated onto the floating (per each fine programming step) can be finely controlled, measured, injected, or "metered" carefully as well, see cols. 11-14. Thus, in so far as programming verification is concerned, the stored charges on the floating gate can be stored, read out, compared, decided, and metered in/out the cell gradually as "increasing" or "decreasing" using programming switches (421), if any, as desired without any complicated circuitry required to one skilled in this art. As a result, charges can be "metered" in or out as recited obviously using just these voltage and/or current switches based on programming time without further complicated circuitry for example.

Regarding claim **28**, Fig. 5 shows that fine programming is carried out right after coarse programming phase;

Regarding claim **33 & 35**, Fig. 4 shows that a plurality programming switches (421) for switching power supplies to the floating gate of such non-volatile cell.

Furthermore, the coarse programming phase/mode does not use any metering charge techniques.

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Regarding claim **36**, Flash or multi-state flash cell has been well discussed in the background of this invention.

- 5. Other claims are allowable over the prior arts of record for the reason as stated below:
 - Claims 29-32 recite the specific conditions and/or sub-steps for the claimed "metering" step which is not suggested or fairly seen elsewhere;
 - Claim 34 recites the use of a "variable" power supply;
 - Claims 37-45 recite the use or specific steps of fine programming process, etc.
- 6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Viet Q. Nguyen whose telephone number is (571) 272-1788. The examiner can normally be reached on 7am-6pm (EST).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Dave Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

V. Nguyen 09/03/2005

> VIET Q. NGUYEN PRIMARY EXAMINER

V. Nquyen